

**3DD512, 3DD515****NPN Silicon Low Frequency High Power Transistor****Features:**

1. Excellent second breakdown capacity. Good temperature stability. Excellent thermal fatigue capability.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for Low-speed switch, low frequency power amplify, power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+

**TECHNICAL DATA:****(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications	
			3DD512	3DD515
Collector-Emitter Voltage	$V_{CEO}$	V	160	200
Emitter-Base Voltage	$V_{EBO}$	V	7	5
Max. Collector Current	$I_{CM}$	A	3	15
Max. Collector Dissipation (Tc=75°C)	$P_{CM}$	W	30	150
Junction Temperature	$T_{jm}$	°C	175	175
Storage Temperature	$T_{stg}$	°C	-55~+175	-65~+175
Emitter-Base Leakage Current	$I_{EBO}$	mA		
Collector-Emitter Leakage Current	$I_{CEO}$	mA	Max.:1.0	Max.:1.0
			$V_{CB}=220V$	$V_{CB}=250V$
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	Max.:1.5	Max.:1.5
			$I_C=1.5A, I_B=0.04A$	$I_C=7.5A, I_B=1.5A$
DC Current Gain	$h_{FE}$		Max.:120, Min.:50	Max.:80, Min.:55
			$V_{CE}= 5V, I_C=2A$	$V_{CE}= 10V, I_C=7.5A$
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	V	220	250
			$I_C=1mA$	$I_C=1mA$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	160	200
			$I_C=2mA$	$I_C=2mA$
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	7	5
			$I_E=5mA$	$I_E=5mA$

**Outline and Dimensions:**